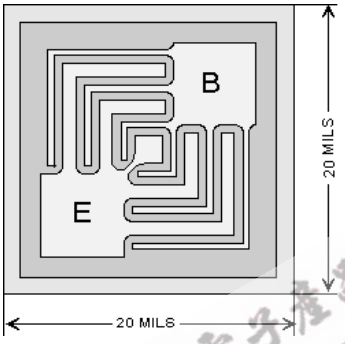
SEMICOA SEMICONDUCTORS

Data Sheet No. 2C2907A

# Chip Type 2C2907A
# Geometry 0600
# Polarity PNP

**Generic Packaged Parts:**

**2N2905, 2N2905A, 2N2907, 2N2907A**




Request Quotation

Chip type **2C2907A** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N2905, 2N2905A, 2N2905AL, 2N2907, 2N2907A, 2N2907AUB, SD2907A, SD2907AF, SQ2907A, SQ2907AF, 2N3486, 2N3486A, 2N6987, 2N6989

**Product Summary:**

**APPLICATIONS:** Designed for general purpose switching and amplifier applications.

**Features:** Radiation graphs available

## Mechanical Specifications

| | | |
|---|---|---|
| **Metallization** | Top | Al - 18 kÅ min. |
| | Backside | Au - 6.5 kÅ nom. |
| **Bonding Pad Size** | Emitter | 4.0 mils x 4.0 mils |
| | Base | 4.0 mils x 4.0 mils |
| **Die Thickness** | 8 mils nominal | |
| **Chip Area** | 20 mils x 20 mils | |
| **Top Surface** | Silox Passivated | |

## Electrical Characteristics
$T_A = 25^oC$

| Parameter | Test conditions | Min | Max | Unit |
|---|---|---|---|---|
| $BV_{CEO}$ | $I_C$ = 10 mA, $I_B$ = 0 | 60 | --- | V dc |
| $BV_{CBO}$ | $I_C$ = 10 µA, $I_E$ = 0 | 60 | --- | V dc |
| $BV_{EBO}$ | $I_E$ = 10 µA, $I_C$ = 0 | 5.0 | --- | V dc |
| $I_{CBO}$ | $V_{CB}$ = 50 V, $I_E$ = 0 | --- | 10 | nA |
| $h_{FE}$ | $I_C$ = 150 mA dc, $V_{CE}$ = 10 V | 100 | 300 | --- |

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 µs, duty cycle less than 2%.*